

Product Description

applications.

Product Specification

PE4135

High Linearity UltraCMOS™ Quad MOSFET Mixer

Features

- Integrated, single-ended RF & LO interfaces
- High linearity: Typical IIP3 at 32dBm 820 - 920 MHz (+17 dBm LO)
- Low conversion loss: 6.8 dB (+17 dBm LO)
- High isolation: Typical LO-IF at 42 dB, LO-RF at 32 dB
- Small 6-lead 3x3 mm DFN package

The PE4135 is manufactured on Peregrine's UltraCMOS™ process, a patented variation of silicon-on-insulator (SOI) technology on a sapphire substrate, offering the performance of GaAs with the economy and integration of conventional CMOS.

The PE4135 is a high linearity passive Quad MOSFET Mixer for GSM800 & Cellular Base Station Receivers, exhibiting high

dynamic range performance over a broad LO drive range of up

to 20 dBm. This mixer integrates passive matching networks to

conversion using low-side LO injection for GSM800 & Cellular Base Station application, and is also suitable for up-conversion

provide single-ended interfaces for the RF and LO ports,

eliminating the need for external RF baluns or matching

networks. The PE4135 is optimized for frequency down-

Figure 1. Functional Diagram

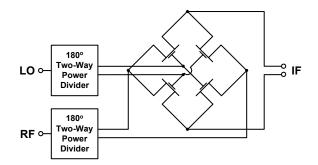


Table 1. Electrical Specifications @ +25 °C

Parameter¹ Minimum Typical Maximum Units Frequency Range: 10 750 850 MHz --RF 820 920 MHz IF² 70 MHz -----Conversion Loss³ 6.8 7.3 dB Isolation: LO-RF 30 32 dB LO-IF 40 42 dB 32 Input IP3 29 dBm Input 1 dB Compression 21 dBm

1. Test conditions unless otherwise noted: IF = 70 MHz, LO input drive = 17 dBm, RF input drive = 3 dBm. Notes:

2. An IF frequency of 70 MHz is a nominal frequency. The IF frequency can be specified by the user as long as the RF and LO frequencies are within the specified maximum and minimum.

3. Conversion Loss includes loss of IF transformer (M/A COM ETC1-1-13, nominal loss 0.7 dB at 70 MHz).





Figure 2. Package Type

6-lead DFN



Figure 3. Pin Configuration (Top View)

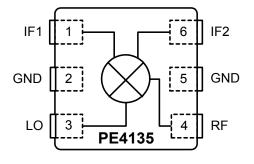


Table 2. Pin Descriptions

Pin No.	Pin Name	Description
1	IF1	IF differential output.
2	GND	Ground connections for Mixer. Traces should be physically short and connect immediately to ground plane for best performance. The exposed solder pad must also be soldered to the ground plane for best performance.
3	LO	LO Input.
4	RF	RF Input.
5	GND	Ground connections for Mixer. Traces should be physically short and connect immediately to ground plane for best performance. The exposed solder pad must also be soldered to the ground plane for best performance.
6	IF2	IF differential output.

Table 3. Absolute Maximum Ratings

Symbol	Parameter/Conditions	Min	Max	Units
T _{ST}	Storage temperature range	-65	150	°C
T _{OP}	Operating temperature range	-40	85	°C
PLO	LO input power		20	dBm
P _{RF}	RF input power		12	dBm
V _{ESD}	ESD Sensitive Device		250	V

Absolute Maximum Ratings are those values listed in the above table. Exceeding these values may cause permanent device damage. Functional operation should be restricted to the limits in the DC Electrical Specifications table. Exposure to absolute maximum ratings for extended periods may affect device reliability.

Electrostatic Discharge (ESD) Precautions

When handling this UltraCMOS[™] device, observe the same precautions that you would use with other ESD-sensitive devices. Although this device contains circuitry to protect it from damage due to ESD, precautions should be taken to avoid exceeding the rating specified in Table 3.

Latch-Up Avoidance

Unlike conventional CMOS devices, UltraCMOS[™] devices are immune to latch-up.



Evaluation Kit

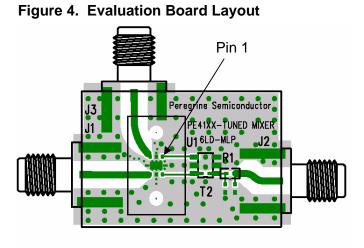


Table 4. Bill of Materials

Reference	Value / Description
T2	M/A Com ETK1-1-13
R1	0Ω
U1	PE4135 MLP Mixer
J1, J2, J3	SMA Connector

Figure 5. Evaluation Board Schematic

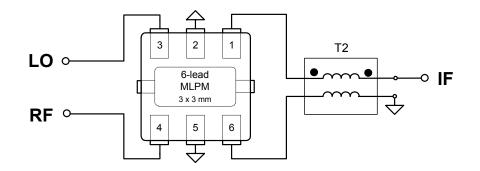
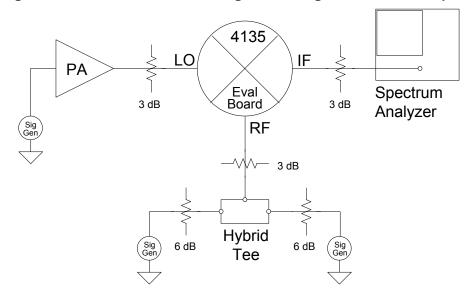


Figure 6. Evaluation Board Testing Block Diagram, 2-Tone Setup



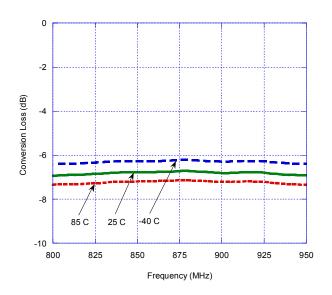
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Typical Performance Data (LO=17 dBm, RF=3 dBm, IF=70 MHz)

Figure 7. Conversion Loss

Figure 8. Input 1dB Compression



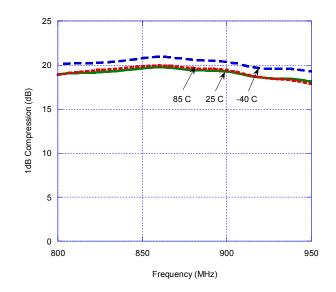


Figure 9. Input IP3 @ 25 °C

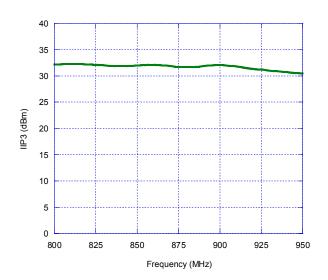
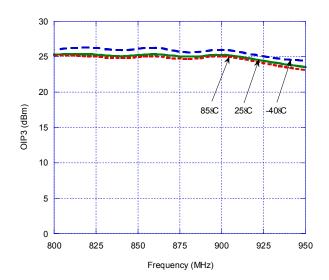


Figure 10. Output IP3

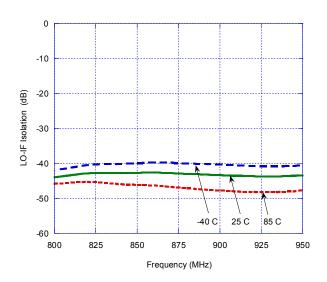




Typical Performance Data (LO=17 dBm, RF=3 dBm, IF=70 MHz)

Figure 11. LO-IF Isolation

Figure 12. LO-RF Isolation



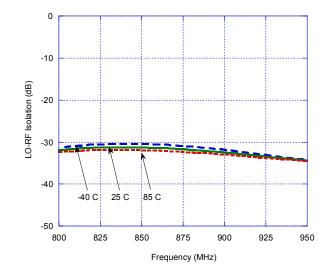


Figure 13. LO Port Return Loss @ 25°C

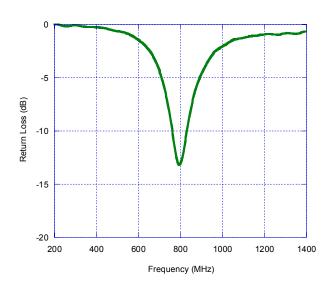
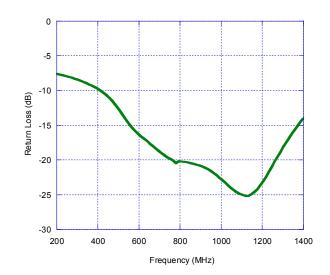


Figure 14. RF Port Return Loss @ 25°C





Typical Performance Data (LO=17 dBm, RF=3 dBm, IF=70 MHz)

Figure 15. Input IP3 Across LO Power

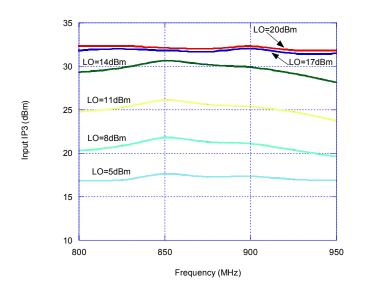


Figure 16. Conversion Loss Across LO Power

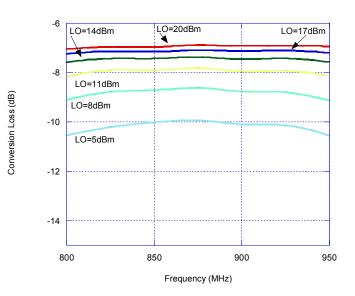


Table 5. Spurious Response

	mRF+nLO			
	nLO			
mRF	1	2	3	4
1	1	29	20	32
2	50	46	58	50
3	69	81	70	77
4	88	85	83	>90

Note: Normalized to dB below PIF

(RF=870 Mhz @ 3 dBm, LO=940 MHz @ 17 dBm)

Table 6. Spurious Response

	mRF+nLO			
	nLO			
mRF	1	2	3	4
1	0	27	12	35
2	47	53	47	50
3	66	66	62	67
4	86	83	>90	>90

Note: Normalized to dB below PIF

(RF=870 Mhz @ 3 dBm, LO=940 MHz @ 17 dBm)



Figure 17. Package Drawing

6-lead DFN

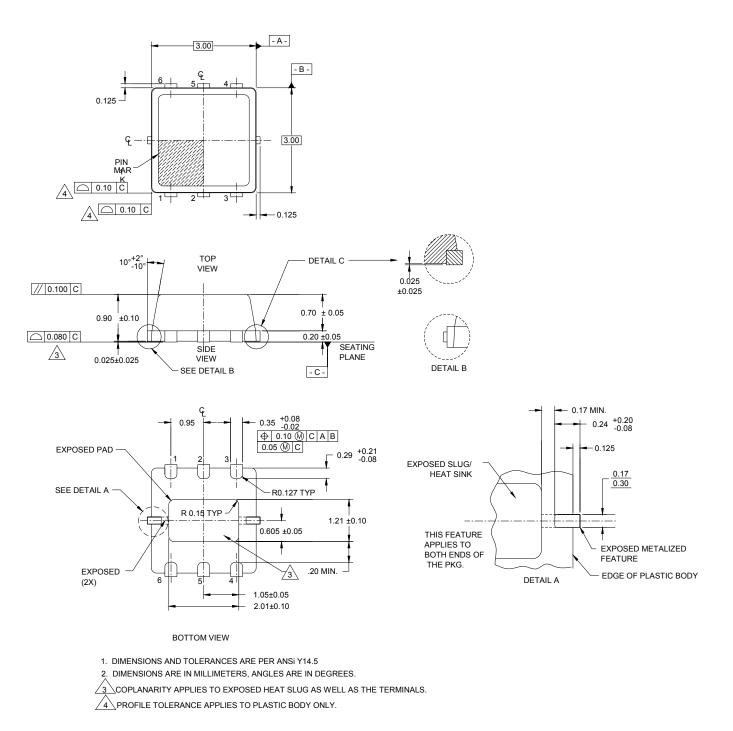




Figure 18. Tape and Reel Specifications

6-lead DFN

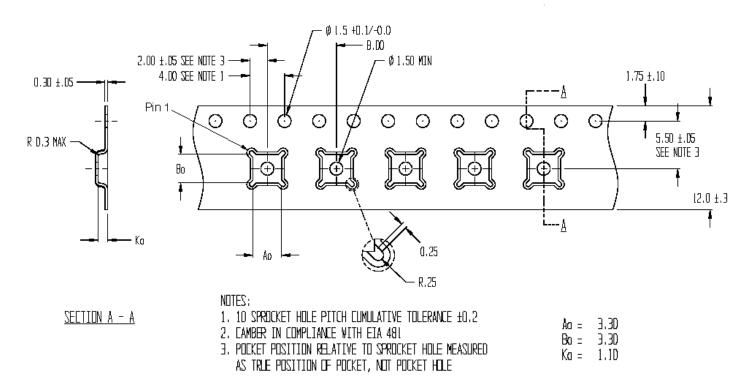


Table 7. Dimensions

Dimension	DFN 3x3 mm
Ao	3.23 ± 0.1
Во	3.17 ± 0.1
Ko	1.37 ± 0.1
Р	4 ± 0.1
W	8 +0.3, -0.1
Т	0.254 ± 0.02
R7 Quantity	3000
R13 Quantity	N.A.

Note: R7 = 7 inch Lock Reel, R13 = 13 inch Lock Reel

Table 8. Ordering Information

Order Code	Part Marking	Description	Package	Shipping Method
4135-01	4135	PE4135-06DFN 3x3mm-12800F	6-lead 3x3 mm DFN	12800 units / Canister
4135-02	4135	PE4135-06DFN 3x3mm-3000C	6-lead 3x3 mm DFN	3000 units / T&R
4135-00	PE4135-EK	PE4135-06DFN 3x3mm-EK	Evaluation Kit	1 / Box
4135-51	4135	PE4135G-06DFN 3x3mm-12800F	Green 6-lead 3x3 mm DFN	12800 units / Canister
4135-52	4135	PE4135G-06DFN 3x3mm-3000C	Green 6-lead 3x3 mm DFN	3000 units / T&R

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Sales Offices

The Americas

Peregrine Semiconductor Corp. 9450 Carroll Park Drive

San Diego, CA 92121 Tel 858-731-9400 Fax 858-731-9499

Europe

Peregrine Semiconductor Europe

Commercial Products: Bâtiment Maine 13-15 rue des Quatre Vents F- 92380 Garches, France Tel: +33-1-47-41-91-73 Fax : +33-1-47-41-91-73 Space and Defense Products:

Space and Defense Products:

180 Rue Jean de Guiramand 13852 Aix-En-Provence cedex 3, France Tel: +33(0) 4 4239 3361 Fax: +33(0) 4 4239 7227

North Asia Pacific

Peregrine Semiconductor K.K.

5A-5, 5F Imperial Tower 1-1-1 Uchisaiwaicho, Chiyoda-ku Tokyo 100-0011 Japan Tel: +81-3-3502-5211 Fax: +81-3-3502-5213

South Asia Pacific

Peregrine Semiconductor

28G, Times Square, No. 500 Zhangyang Road, Shanghai, 200122, P.R. China Tel: +86-21-5836-8276 Fax: +86-21-5836-7652

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Data Sheet Identification

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